

GaAs/GaAs Infrared Chip ---TK0A08IRG

1. Scope

- The specification applies to GaAs infrared chips .
- Type : TK0A08IRG.

2. Structure

- GaAs/GaAs infrared chip.
- P/N mesa type.
- Smooth surface side wall roughing.
- Electrode P (anode) side : Aluminum or Gold.
- Electrode N (cathode) side : Gold alloy.

3. Size

- Chip size : 195 μm \times 195 μm
- Chip height : 220 μm \pm 30 μm
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

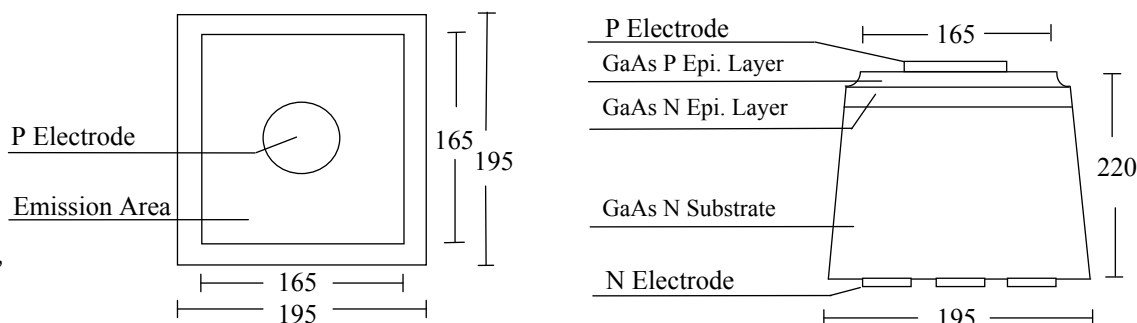
(T_a = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V _F	I _F = 20mA		1.27	1.35	V
Reverse Voltage	V _R	I _R = 10 μA	5			V
Radiant Power	P _O	I _F = 20mA	0.8			mw
Peak Wavelength	λ_p	I _F = 20mA		940		nm
Spectrum Width of Half Value	$\Delta\lambda$	I _F = 20mA		50		nm

5. Application

- Interrupter module, Photo coupler, Mouse, Telephone.

Bin	TK0A08IRG		
	MIN	TYP	MAX
B	0.90	1.00~1.09	1.20
C	0.95	1.10~1.19	1.30



Unit : μm

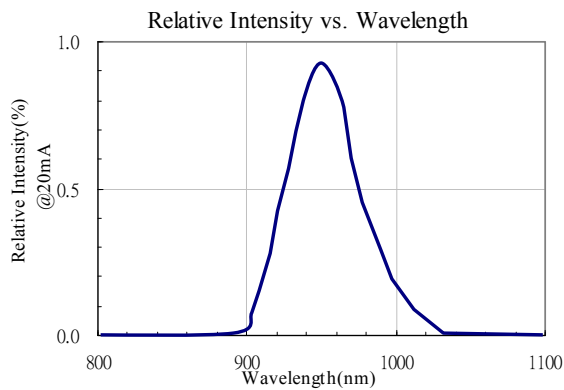
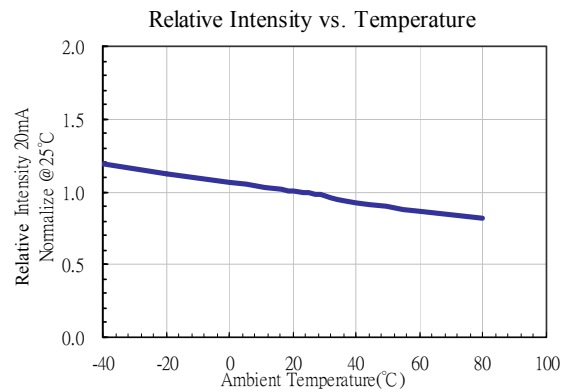
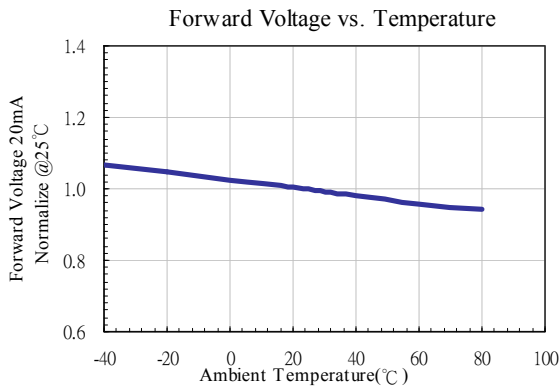
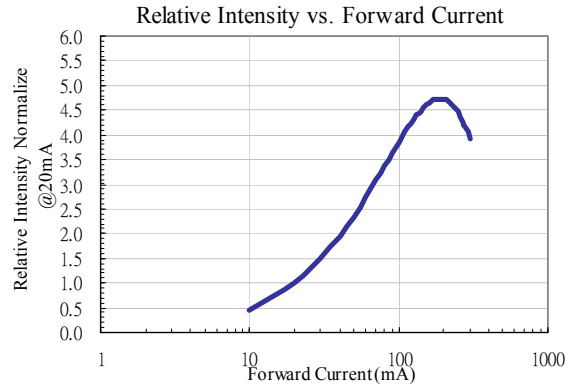
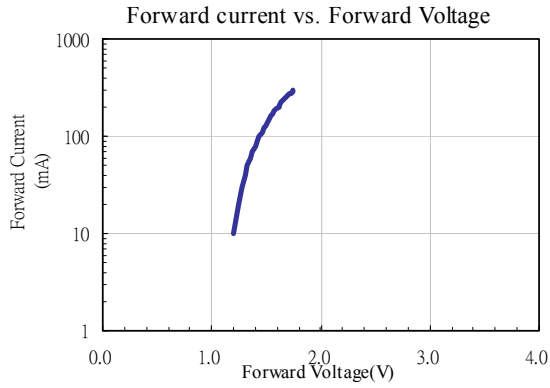
fig. 1

2015.Mar



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Electro-Optical Characteristics Curve



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